

查询ARF771LTS45供应商

捷多邦 PCB打样工厂, 24小时加急出货

POSEICO

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FAST RECOVERY DIODE

ARF771LT

FOR IGBT, IEGT, GCT APPLICATIONS

SNUBBERLESS OPERATION

LOW LOSSES SOFT RECOVERY

Repetitive voltage up to

4500 V

Mean forward current

1730 A

Surge current

28 kA

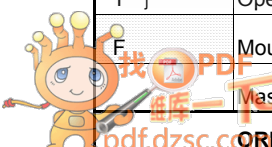
TARGET SPECIFICATION

mar 03 - ISSUE : 2

Symbol	Characteristic	Conditions	T _j [°C]	Value	Unit
BLOCKING					
V _{RRM}	Repetitive peak reverse voltage		140	4500	V
V _{RSM}	Non-repetitive peak reverse voltage		140	4600	V
I _{RRM}	Repetitive peak reverse current	V=VRRM	140	150	mA
V _{DC LINK}	Permanent DC voltage		140	2800	V
CONDUCTING					
I _{F (AV)}	Mean forward current	180° sin ,50 Hz, Th=55°C, double side cooled		1730	A
I _{F (AV)}	Mean forward current	180° square, 50 Hz, Th=55°C, double side cooled		1790	A
I _{FSM}	Surge forward current	Sine wave, 10 ms	140	28	kA
I ² t	I ² t	reapplied reverse voltage up to 50% VRSM		3920 x1E3	A²s
V _{FM}	Forward voltage	Forward current = 2500 A	140	3.95	V
V _{F(TO)}	Threshold voltage		140	1.95	V
r _F	Forward slope resistance		140	0.800	mohm
SWITCHING					
Q _{rr}	Reverse recovery charge	I _F = 2500 A di/dt = 250 A/μs VR = 100 V	140	2400	μC
I _{rr}	Peak reverse recovery current		140		A
t _{rr}	Reverse recovery time	I _F = 2500 A			μs
Q _{rr}	Reverse recovery charge	di/dt = 1000 A/μs VR = 2800 V		3500	μC
I _{rr}	Peak reverse recovery current		140	1500	A
s	Softness (s-factor), min				
E _{OFF}	Turn off energy dissipation			7	J
V _{FR}	Peak forward recovery	di/dt = 500 A/μs	140	65	V
MOUNTING					
R _{th(j-h)}	Thermal impedance	Junction to heatsink, double side cooled		9.5	°C/kW
R _{th(c-h)}	Thermal impedance	Case to heatsink, double side cooled		2	°C/kW
T _j	Operating junction temperature			-30 / 140	°C
F	Mounting force			46.0 / 54.0	kN
m	Mass			1150	g

ORDERING INFORMATION : ARF771LT S 45

standard specification _____ VRRM/100

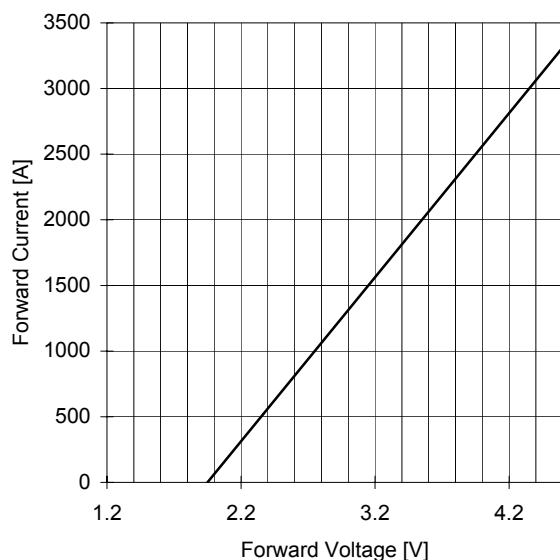


ARF771LT FAST RECOVERY DIODE

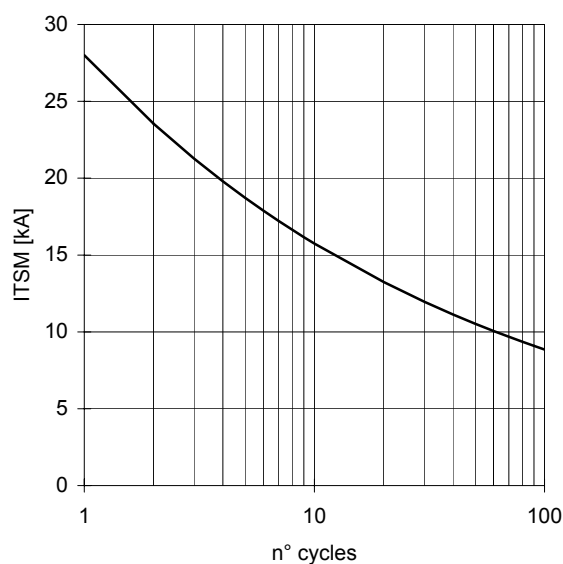


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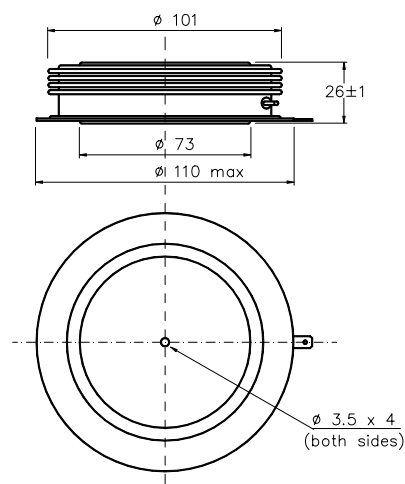
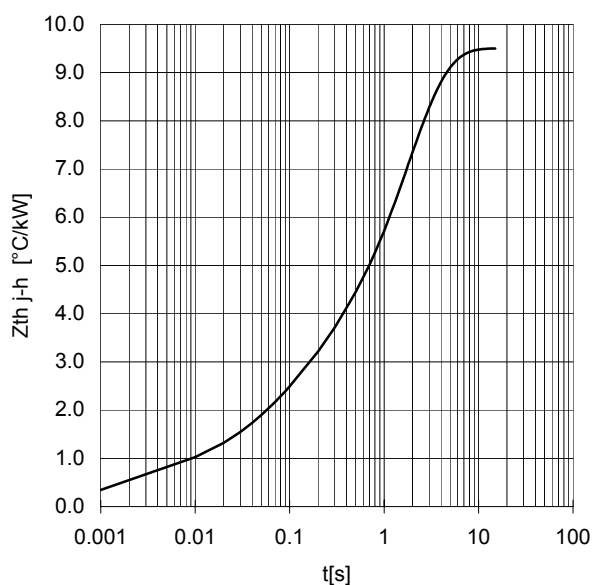
FORWARD CHARACTERISTIC
 $T_j = 140^\circ\text{C}$



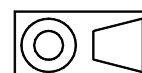
SURGE CHARACTERISTIC
 $T_j = 140^\circ\text{C}$



TRANSIENT THERMAL IMPEDANCE
DOUBLE SIDE COOLED



Dimensions
in mm



All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink, surfaces with flatness $< .03 \text{ mm}$ and roughness $< 2 \mu\text{m}$.

In the interest of product improvement POSEICO reserves the right to change any data given in this data sheet at any time without previous notice.

If not stated otherwise the maximum value of ratings (symbols over shaded background) and characteristics is reported.

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